

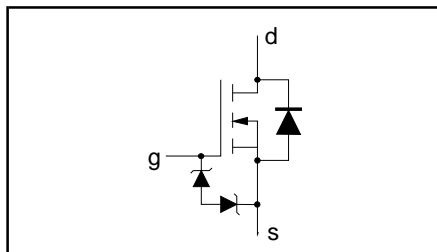
# TrenchMOS™ transistor Logic level FET

## PHP130N03LT, PHB130N03LT

### FEATURES

- 'Trench' technology
- Very low on-state resistance
- Fast switching
- Stable off-state characteristics
- High thermal cycling performance
- Low thermal resistance

### SYMBOL



### QUICK REFERENCE DATA

$V_{DSS} = 30\text{ V}$
$I_D = 75\text{ A}$
$R_{DS(ON)} \leq 6\text{ m}\Omega (V_{GS} = 5\text{ V})$
$R_{DS(ON)} \leq 5\text{ m}\Omega (V_{GS} = 10\text{ V})$

### GENERAL DESCRIPTION

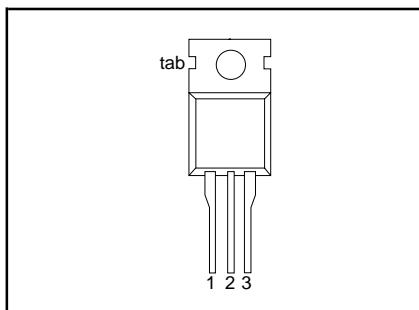
N-channel enhancement mode logic level field-effect power transistor in a plastic envelope using 'trench' technology. The device has very low on-state resistance. It is intended for use in dc to dc converters and general purpose switching applications.

The PHP130N03LT is supplied in the SOT78 (TO220AB) conventional leaded package.  
The PHB130N03LT is supplied in the SOT404 surface mounting package.

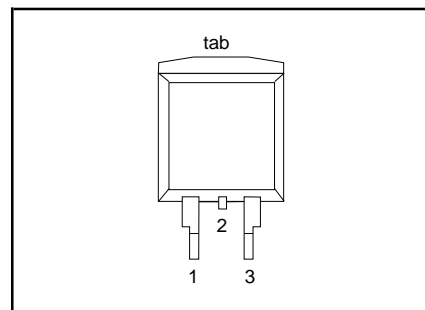
### PINNING

PIN	DESCRIPTION
1	gate
2	drain <sup>1</sup>
3	source
tab	drain

### SOT78 (TO220AB)



### SOT404



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DSS}$	Drain-source voltage	$T_j = 25\text{ }^\circ\text{C to }175\text{ }^\circ\text{C}$	-	30	V
$V_{DGR}$	Drain-gate voltage	$T_j = 25\text{ }^\circ\text{C to }175\text{ }^\circ\text{C}; R_{GS} = 20\text{ k}\Omega$	-	30	V
$V_{GS}$	Gate-source voltage		-	$\pm 13$	V
$I_D$	Continuous drain current	$T_{mb} = 25\text{ }^\circ\text{C}; V_{GS} = 5\text{ V}$	-	75	A
		$T_{mb} = 100\text{ }^\circ\text{C}; V_{GS} = 5\text{ V}$	-	75	A
$I_{DM}$	Pulsed drain current	$T_{mb} = 25\text{ }^\circ\text{C}$	-	240	A
$P_D$	Total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$	-	187	W
$T_j, T_{stg}$	Operating junction and storage temperature		-55	175	$^\circ\text{C}$

<sup>1</sup> It is not possible to make connection to pin 2 of the SOT404 package.

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### ESD LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_C$	Electrostatic discharge capacitor voltage, all pins	Human body model (100 pF, 1.5 k $\Omega$ )	-	2	kV

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base		-	-	0.8	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	SOT78 package, in free air SOT404 package, pcb mounted, minimum footprint	-	60	-	K/W
			-	50	-	K/W

### ELECTRICAL CHARACTERISTICS

$T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA};$ $T_j = -55^\circ\text{C}$	30 27	-	-	V V
$V_{(BR)GSS}$	Gate-source breakdown voltage	$I_G = 1\text{ mA}$	10	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}$ $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$	1 0.5 -	1.5 -	2 -	V V V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 5\text{ V}; I_D = 25\text{ A}$ $V_{GS} = 10\text{ V}; I_D = 25\text{ A}$ $V_{GS} = 5\text{ V}; I_D = 25\text{ A}; T_j = 175^\circ\text{C}$	- - -	5 4.5	6 5 11	m $\Omega$ m $\Omega$ m $\Omega$
$g_{fs}$	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 25\text{ A}$	20	40	-	S
$I_{GSS}$	Gate-source leakage current	$V_{GS} = \pm 5\text{ V}; V_{DS} = 0\text{ V};$ $T_j = 175^\circ\text{C}$	-	0.02	1	$\mu\text{A}$ $\mu\text{A}$
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 30\text{ V}; V_{GS} = 0\text{ V};$ $T_j = 175^\circ\text{C}$	-	0.05	10	$\mu\text{A}$ $\mu\text{A}$
$Q_{g(tot)}$	Total gate charge	$I_D = 75\text{ A}; V_{DD} = 24\text{ V}; V_{GS} = 5\text{ V}$	-	92	-	nC
$Q_{gs}$	Gate-source charge		-	10	-	nC
$Q_{gd}$	Gate-drain (Miller) charge		-	36	-	nC
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 15\text{ V}; I_D = 25\text{ A};$	-	45	60	ns
$t_r$	Turn-on rise time	$V_{GS} = 5\text{ V}; R_G = 5\ \Omega$	-	120	170	ns
$t_{d\ off}$	Turn-off delay time	Resistive load	-	225	300	ns
$t_f$	Turn-off fall time		-	100	135	ns
$L_d$	Internal drain inductance	Measured tab to centre of die	-	3.5	-	nH
$L_d$	Internal drain inductance	Measured from drain lead to centre of die (SOT78 package only)	-	4.5	-	nH
$L_s$	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	5000	-	pF
$C_{oss}$	Output capacitance		-	1150	-	pF
$C_{rss}$	Feedback capacitance		-	500	-	pF

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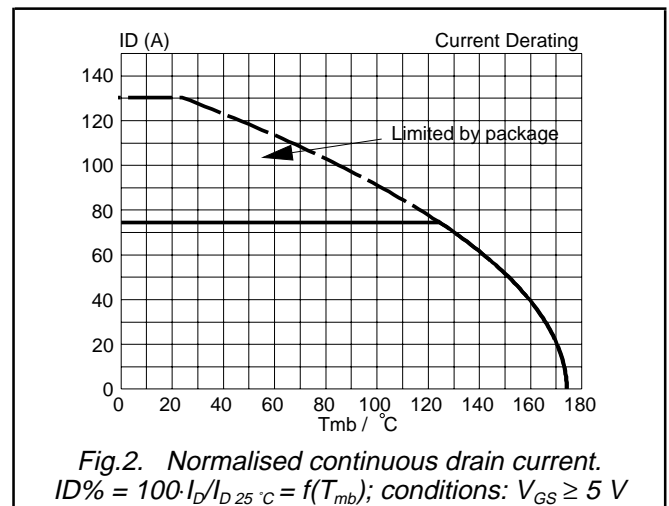
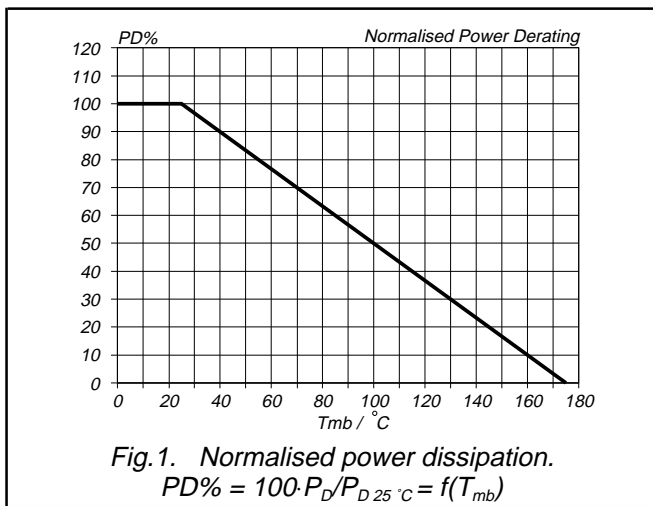
**REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS**

T<sub>j</sub> = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>S</sub>	Continuous source current (body diode)		-	-	75	A
I <sub>SM</sub>	Pulsed source current (body diode)		-	-	240	A
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 25 A; V <sub>GS</sub> = 0 V I <sub>F</sub> = 75 A; V <sub>GS</sub> = 0 V	-	0.85 1.0	1.2 -	V
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 75 A; -di <sub>F</sub> /dt = 100 A/μs; V <sub>GS</sub> = -10 V; V <sub>R</sub> = 25 V	-	100	-	ns
Q <sub>rr</sub>	Reverse recovery charge		-	0.6	-	μC

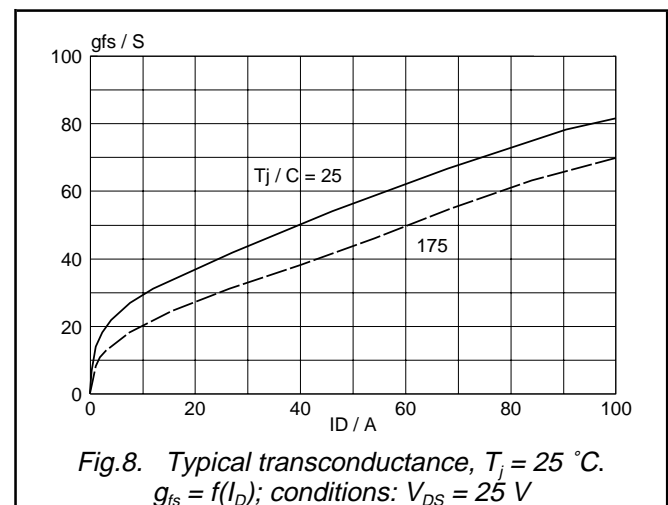
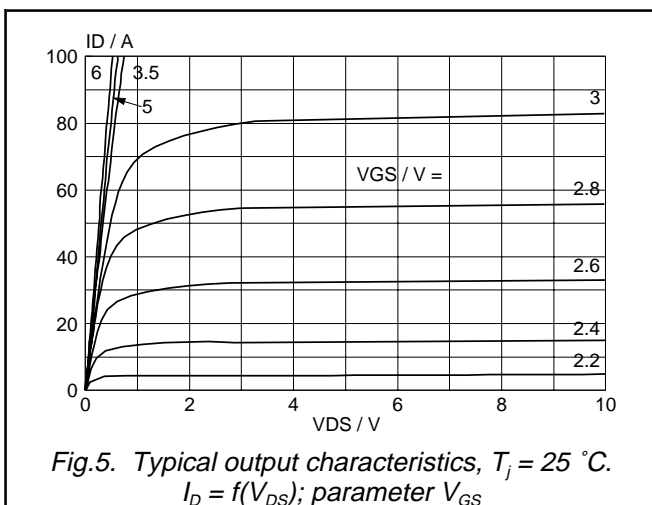
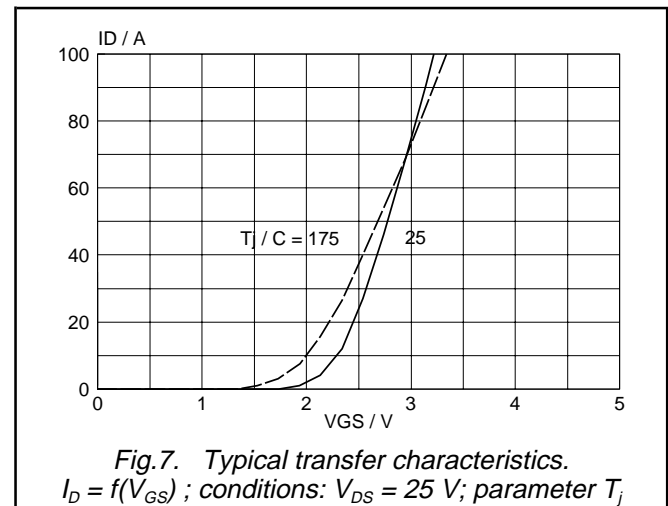
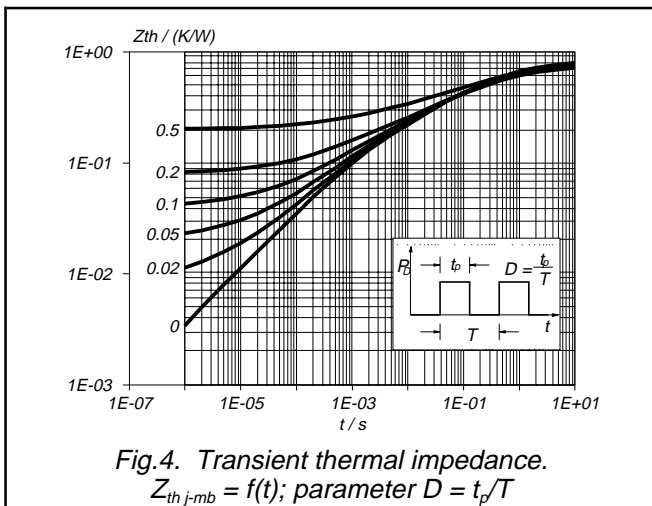
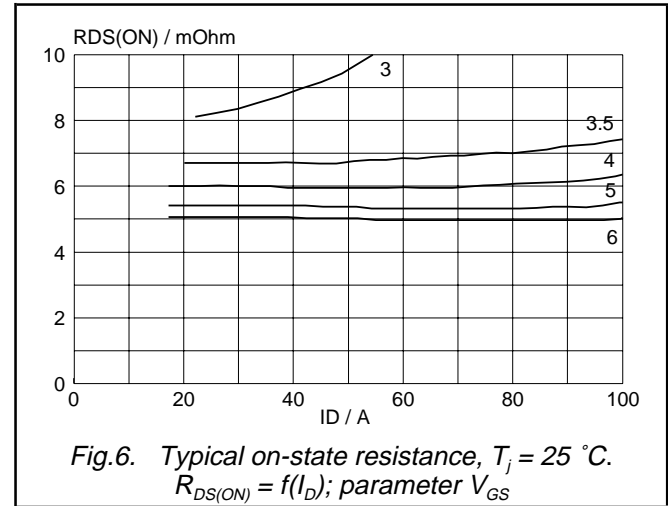
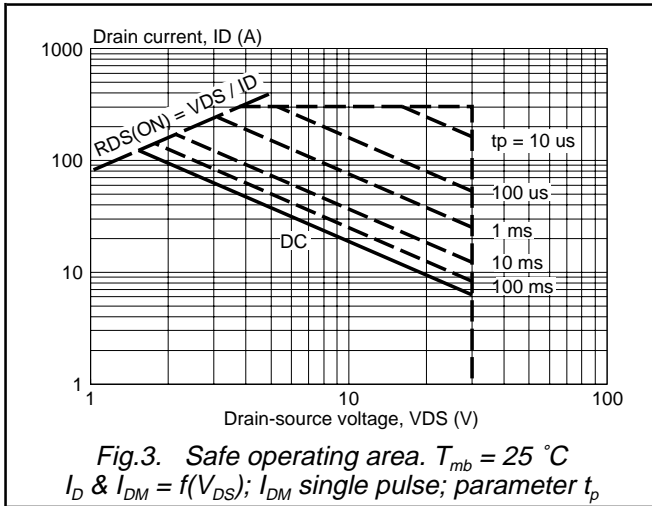
**AVALANCHE LIMITING VALUE**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
W <sub>DSS</sub>	Drain-source non-repetitive unclamped inductive turn-off energy	I <sub>D</sub> = 75 A; V <sub>DD</sub> ≤ 15 V; V <sub>GS</sub> = 5 V; R <sub>GS</sub> = 50 Ω; T <sub>mb</sub> = 25 °C	-	500	mJ



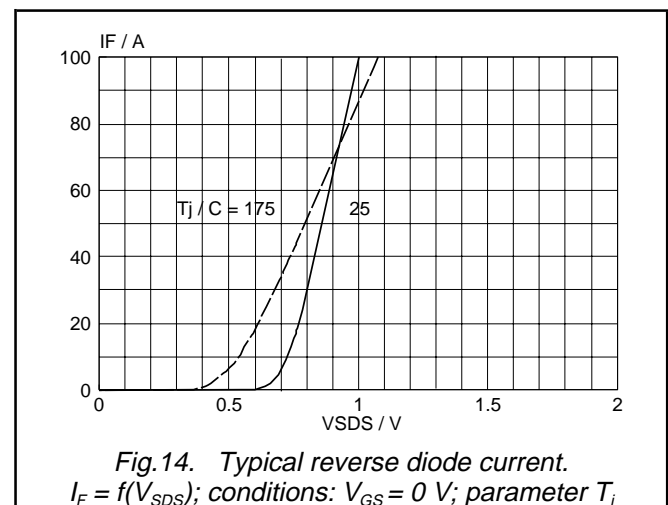
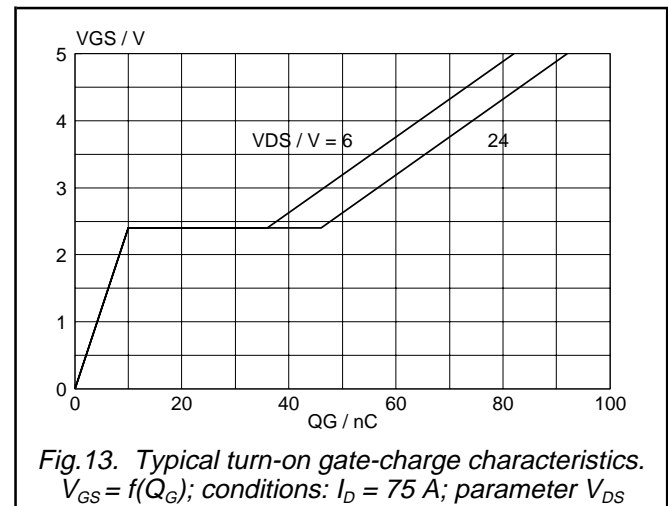
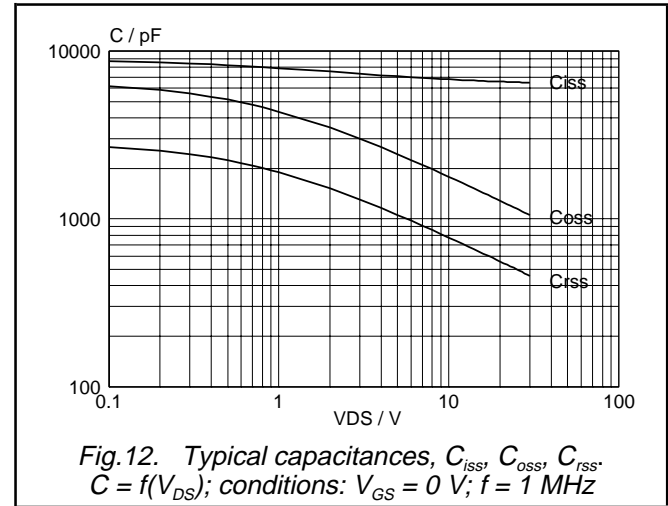
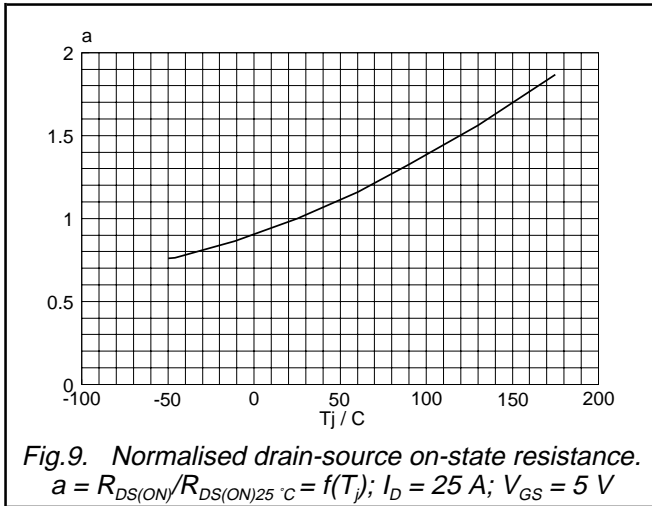
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